

METHODS OF THIN FILM PROCESS

ABSTRACT OF THE DISCLOSURE

A method for forming a semiconductor structure includes forming a plurality of features across a surface of a substrate, with at least one space being between two adjacent features. A first dielectric layer is formed on the features and within the at least one space. A portion of the first dielectric layer interacts with a reactant derived from a first precursor and a second precursor to form a first solid product. The first solid product is decomposed to substantially remove the portion of the first dielectric layer. A second dielectric layer is formed to substantially fill the at least one space.

Figure 2